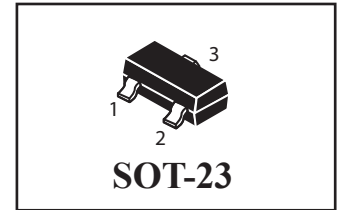
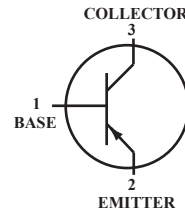


Switching Transistor PNP Silicon



Maximum Ratings

| Rating | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Emitter Voltage | V _{CEO} | -40 | Vdc |
| Collector-Base Voltage | V _{CBO} | -40 | Vdc |
| Emitter-Base Voltage | V _{EBO} | -5.0 | Vdc |
| Collector Current-Continuous | I _C | -600 | mAdc |

Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|--|----------------------|-------------|------|
| Total Device Dissipation FR-5 Board ⁽¹⁾ TA=25°C Derate above 25°C | P _D | 225 | mW |
| Thermal Resistance, Junction to Ambient | R _{θJA} | 556 | °C/W |
| Total Device Dissipation Alumina Substrate, ⁽²⁾ TA=25°C Derate above 25°C | P _D | 300 | mW |
| Thermal Resistance, Junction to Ambient | R _{θJA} | 417 | °C/W |
| Junction and Storage, Temperature | T _{J, Tstg} | -55 to +150 | °C |

Device Marking

MMBT4403=2T

Electrical Characteristics (TA=25°C Unless Otherwise noted)

| Characteristics | Symbol | Min | Max | Unit |
|-----------------|--------|-----|-----|------|
|-----------------|--------|-----|-----|------|

Off Characteristics

| | | | | |
|--|------------------|------|------|------|
| Collector-Emitter Breakdown Voltage ⁽³⁾ (I _C =-1.0mAdc, I _B =0) | V(BR)CEO | -40 | - | Vdc |
| Collector-Base Breakdown Voltage (I _C =-0.1mAdc, I _E =0) | V(BR)CBO | -40 | - | Vdc |
| Emitter-Base Breakdown Voltage (I _E =-0.1mAdc, I _C =0) | V(BR)EBO | -5.0 | - | Vdc |
| Base Cutoff Current (V _{CE} =-35 Vdc, V _{EB} =-0.4 Vdc) | I _{BEV} | - | -0.1 | uAdc |
| Collector Cutoff Current (V _{CE} =-35Vdc, V _{EB} =-0.4Vdc) | I _{CEX} | - | -0.1 | uAdc |

1.FR-5=1.0 x 0.75 x 0.062 in.

2.Alumina=0.4 x 0.3 x 0.024 in. 99.5% alumina.

3.Pulse Test:Pulse Width ≤300 μS, Duty Cycle ≤2.0%.

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted) (Continued)

| Characteristics | Symbol | Min | Max | Unit |
|-----------------|--------|-----|-----|------|
|-----------------|--------|-----|-----|------|

On Characteristics (3)

| | | | | |
|--|---------------|------------------------------|--------------------|-----|
| DC Current Gain ($I_C = -0.1 \text{ mA}$, $V_{CE} = -1.0 \text{ Vdc}$) ($I_C = -1.0 \text{ mA}$, $V_{CE} = -1.0 \text{ Vdc}$) ($I_C = -10 \text{ mA}$, $V_{CE} = -1.0 \text{ Vdc}$) ($I_C = 150 \text{ mA}$, $V_{CE} = -2.0 \text{ Vdc}$) ⁽³⁾ ($I_C = -500 \text{ mA}$, $V_{CE} = -2.0 \text{ Vdc}$) ⁽³⁾ | H_{FE} | 30 60 100 100 20 | . . 300 . | - |
| Collector-Emitter Saturation Voltage (3) ($I_C = -150 \text{ mA}$, $I_B = -15 \text{ mA}$) ($I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$) | $V_{CE(sat)}$ | . . | -0.4 -0.75 | Vdc |
| Base-Emitter Saturation Voltage (3) ($I_C = -150 \text{ mA}$, $I_B = -15 \text{ mA}$) ($I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$) | $V_{BE(sat)}$ | -0.75 | -0.95 -1.3 | Vdc |

Small-signal Characteristics

| | | | | |
|---|----------|-----|-----|------------------|
| Current-Gain-Bandwidth Product (4) ($I_C = -20 \text{ mA}$, $V_{CE} = -10 \text{ Vdc}$, $f = 100 \text{ MHz}$) | f_T | 200 | - | MHz |
| Collector-Base Capacitance ($V_{CB} = -10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$) | C_{cb} | - | 8.5 | pF |
| Emitter-Base Capacitance ($V_{EB} = -0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$) | C_{eb} | - | 30 | pF |
| Input Impedance ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mA}$, $f = 1.0 \text{ kHz}$) | h_{ie} | 1.5 | 15 | k ohms |
| Voltage Feedback Ratio ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mA}$, $f = 1.0 \text{ kHz}$) | h_{re} | 0.1 | 8 | $\times 10^{-4}$ |
| Small-Signal Current Gain ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mA}$, $f = 1.0 \text{ kHz}$) | h_{fe} | 60 | 500 | . |
| Output Admittance ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mA}$, $f = 1.0 \text{ kHz}$) | h_{oe} | 1.0 | 100 | μmhos |

Switching Characteristics

| | | | | | |
|--------------|---|----|---|-----|----|
| Delay Time | (Vcc = -30 Vdc, VEB = -2.0 Vdc Ic = -150 mA, IB1 = -15 mA) | td | - | 15 | ns |
| Rise Time | | tr | - | 20 | |
| Storage Time | (Vcc = -30 Vdc, Ic = -150 mA, IB1 = IB2 = -15 mA) | ts | - | 225 | ns |
| Fall Time | | tf | - | 30 | |

SWITCHING TIME EQUIVALENT TEST CIRCUIT

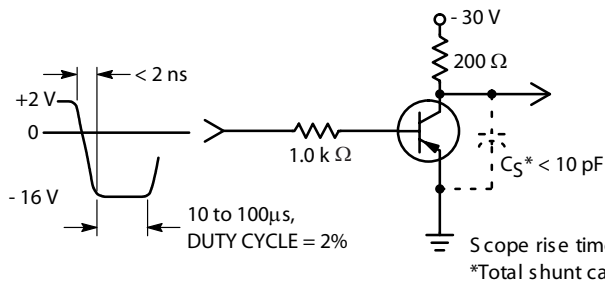


Figure 1. Turn-On Time

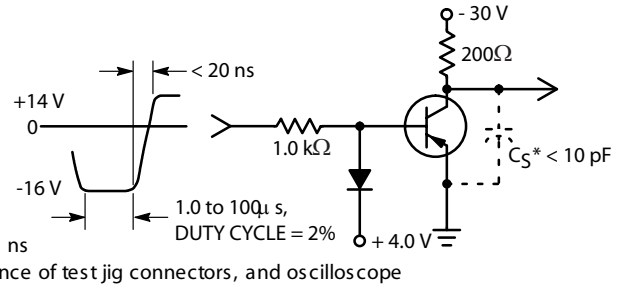


Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

— 25 °C - - - 105 °C

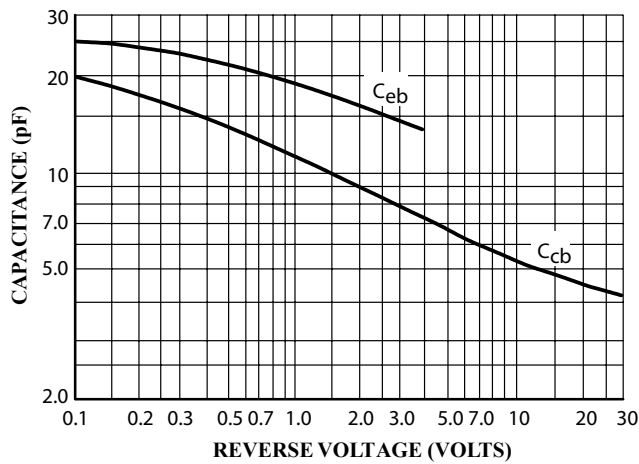


Figure 3. Capacitances

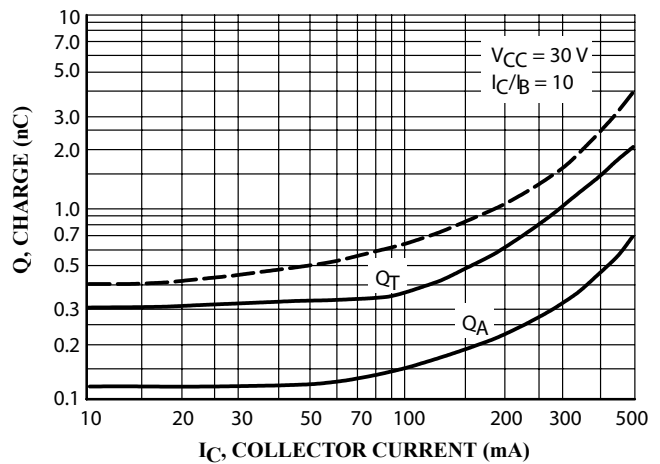


Figure 4. Charge Data

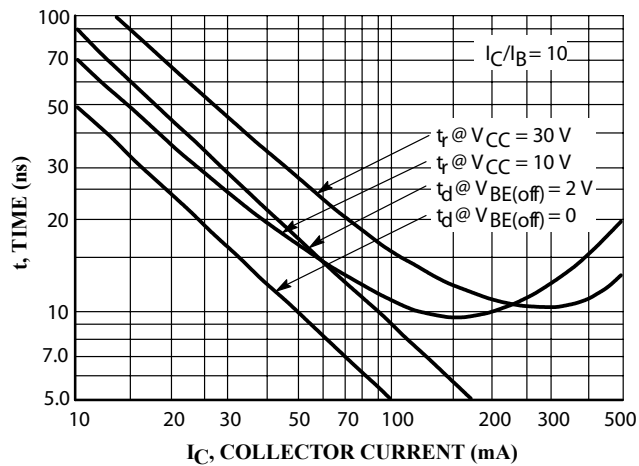


Figure 5. Turn-On Time

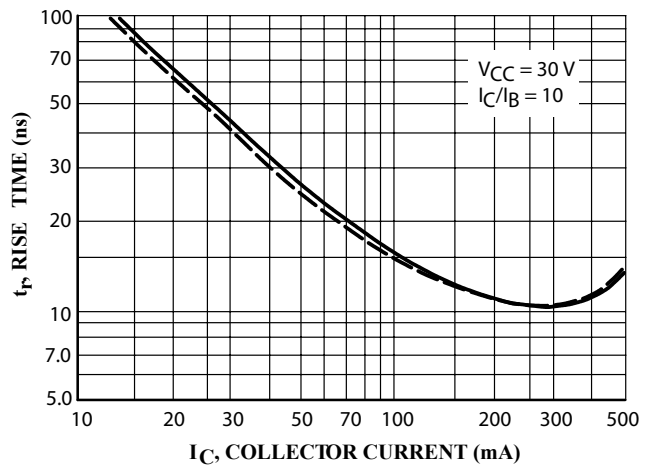


Figure 6. Rise Time

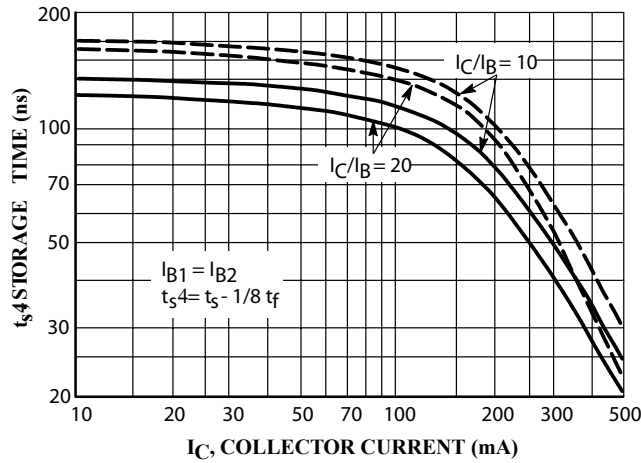


Figure 7. Storage Time

h P PARAMETERS

$V_{CE} = \pm 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ \text{C}$

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To

obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly-numbered curves on each graph.

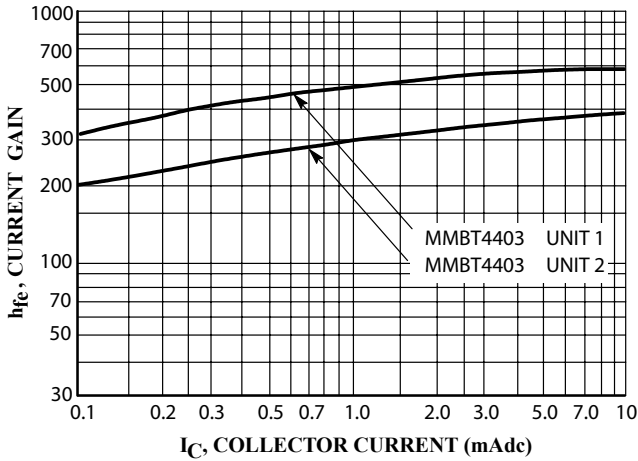


Figure 10. Current Gain

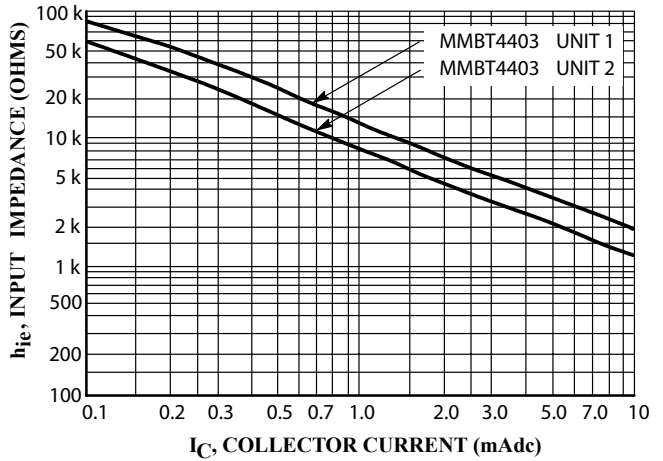


Figure 11. Input Impedance

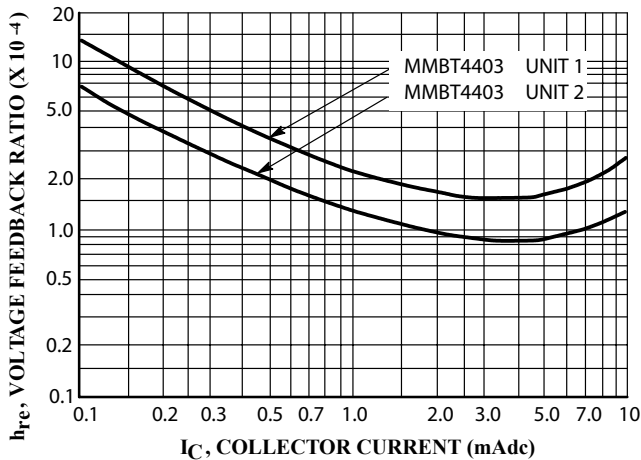


Figure 12. Voltage Feedback Ratio

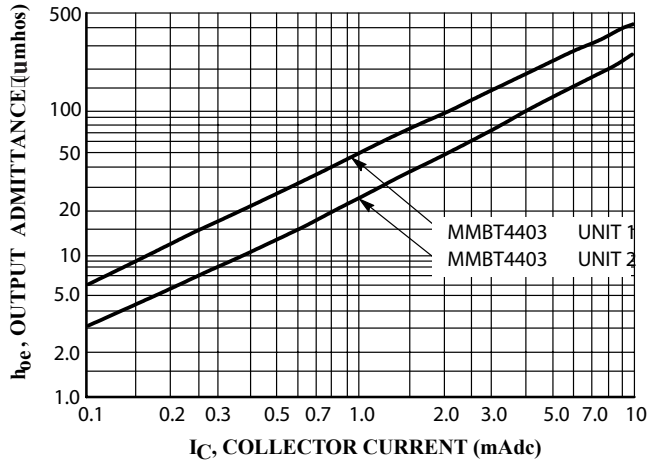


Figure 13. Output Admittance

STATIC CHARACTERISTICS

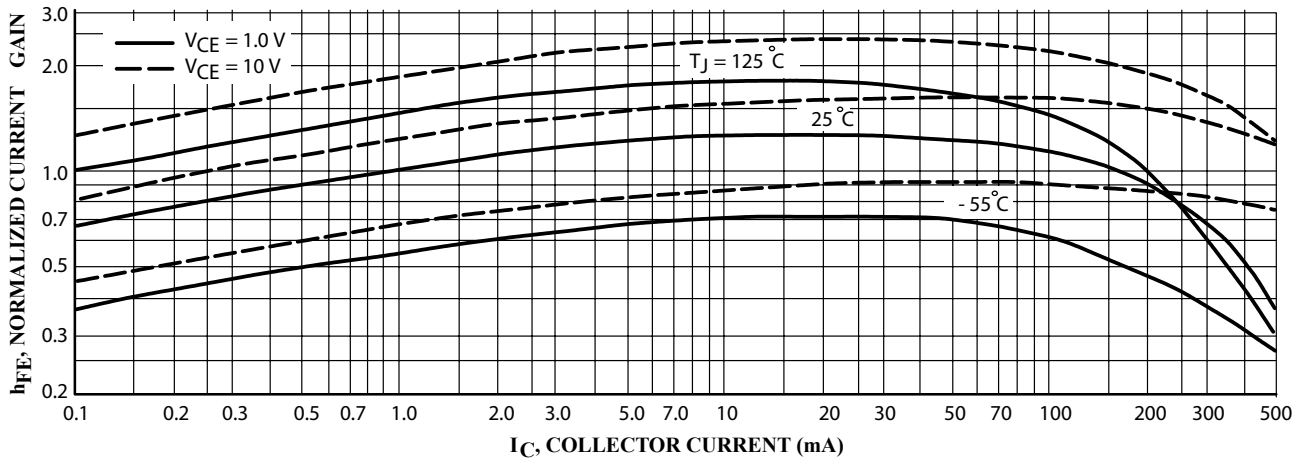


Figure 14. DC Current Gain

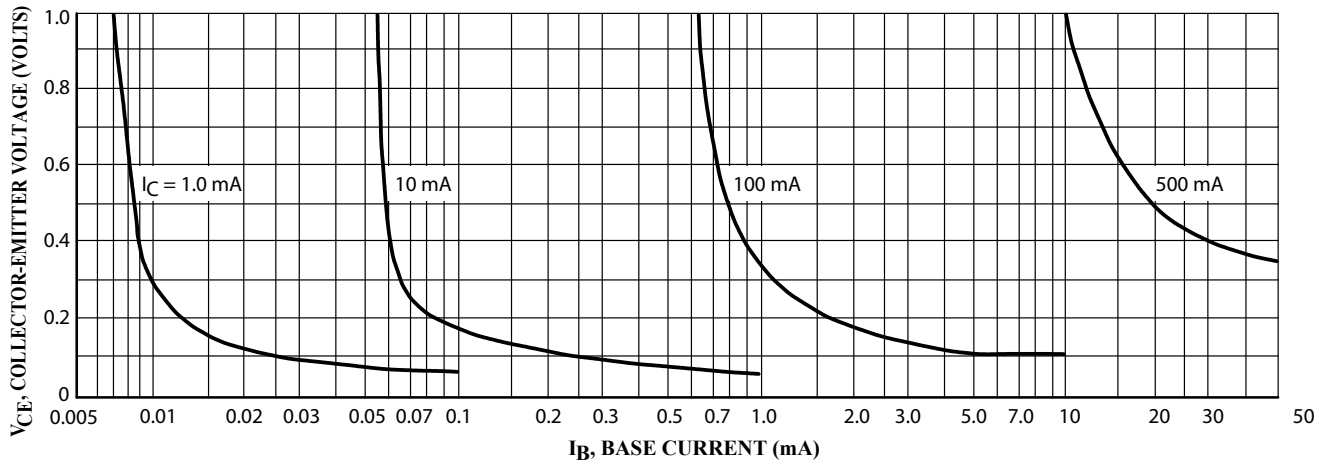


Figure 15. Collector Saturation Region

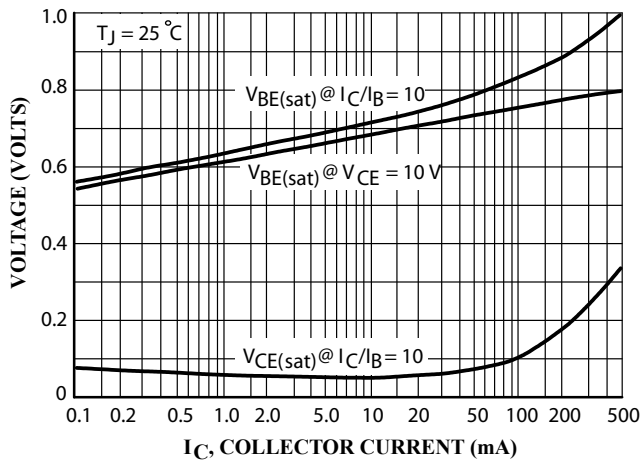


Figure 16. "On" Voltages

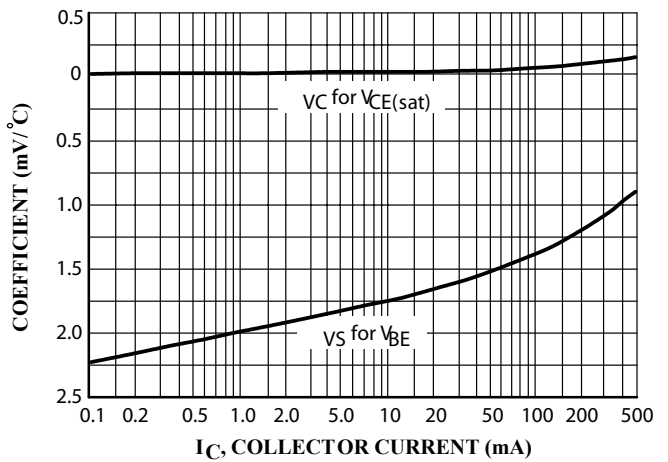
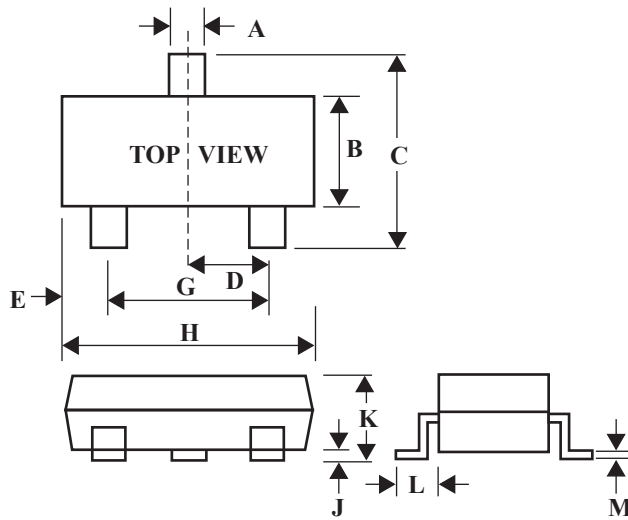


Figure 17. Temperature Coefficients

SOT-23 Package Outline Dimensions

Unit:mm



| Dim | Min | Max |
|-----|-------|------|
| A | 0.35 | 0.51 |
| B | 1.19 | 1.40 |
| C | 2.10 | 3.00 |
| D | 0.85 | 1.05 |
| E | 0.46 | 1.00 |
| G | 1.70 | 2.10 |
| H | 2.70 | 3.10 |
| J | 0.01 | 0.13 |
| K | 0.89 | 1.10 |
| L | 0.30 | 0.61 |
| M | 0.076 | 0.25 |